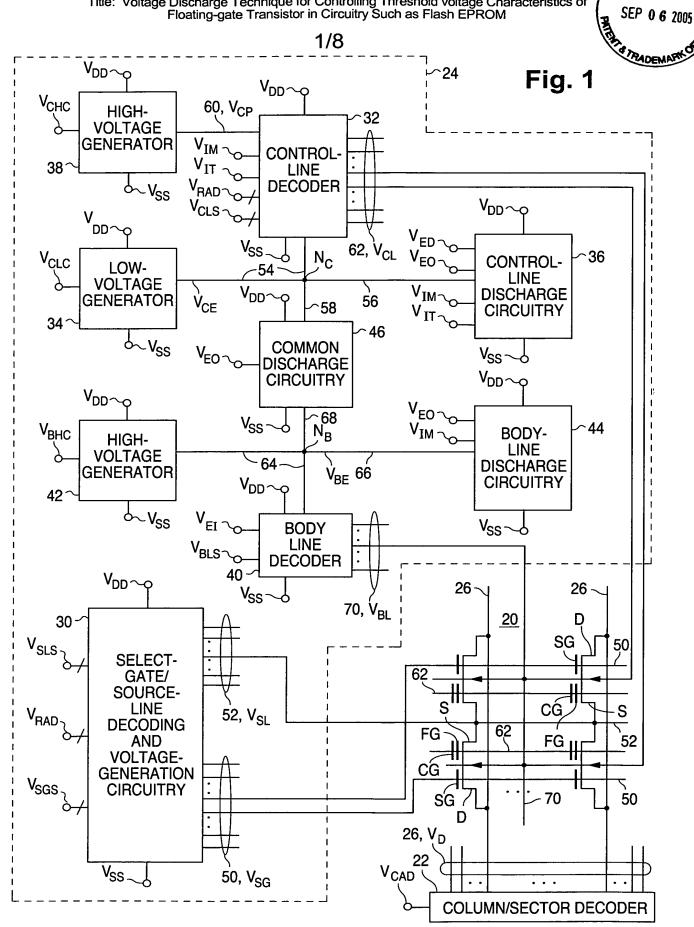
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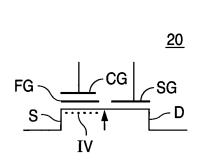


Fig. 2

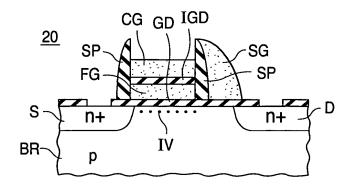


Fig. 3

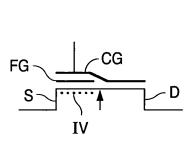


Fig. 6a

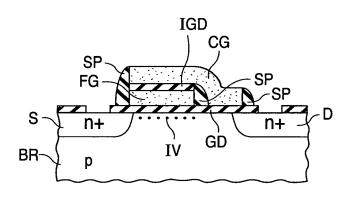


Fig. 7a

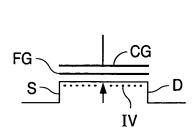


Fig. 7a

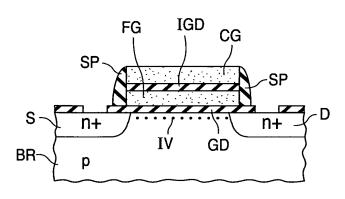
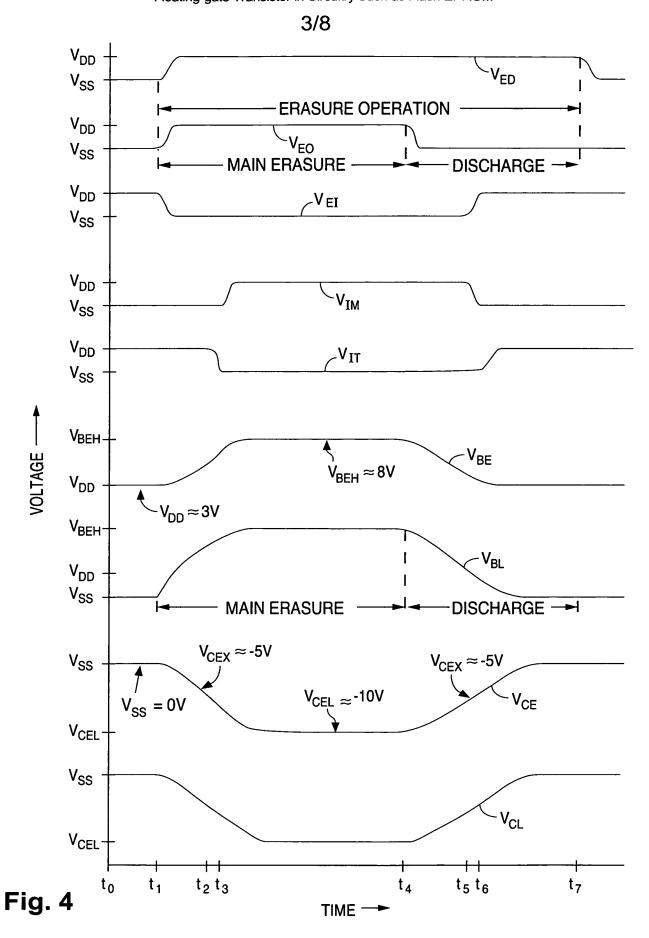


Fig. 7b



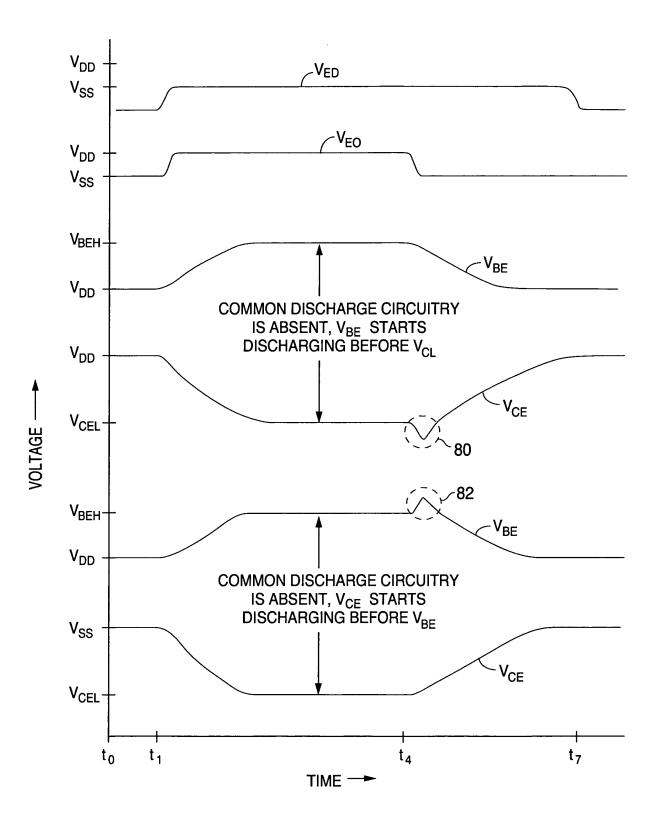
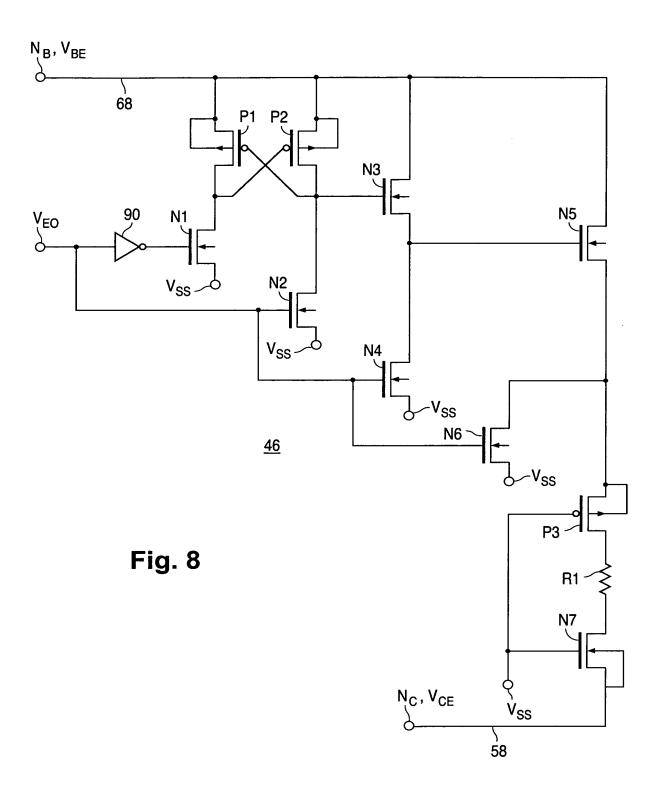


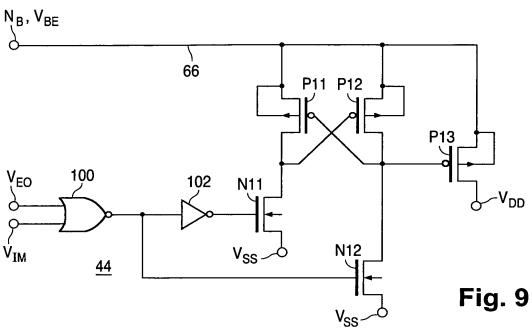
Fig. 5

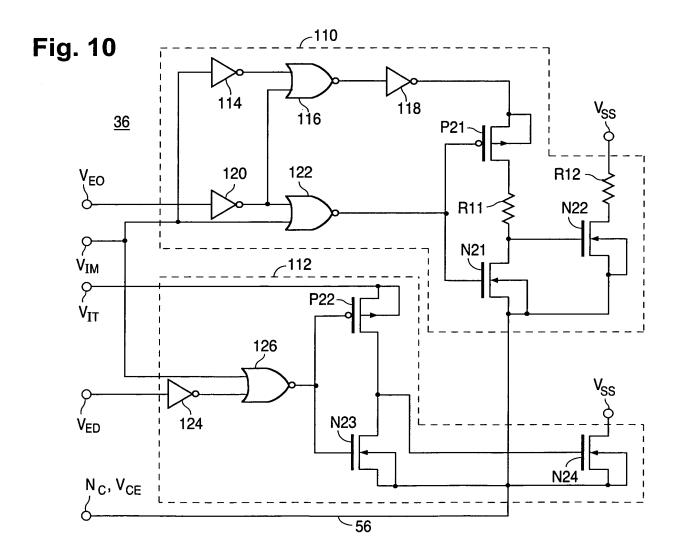


REPLACEMENT SHEET

NT SHEET
R-0004
Inventor: Park, Jongmin Appl'n No.: 10/780,030
Title: Voltage Discharge Technique for Controlling Threshold voltage Characteristics of Floating-gate Transistor in Circuitry Such as Flash EPROM







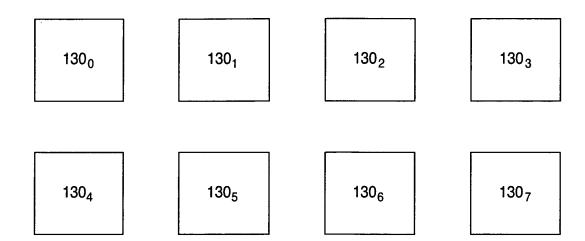
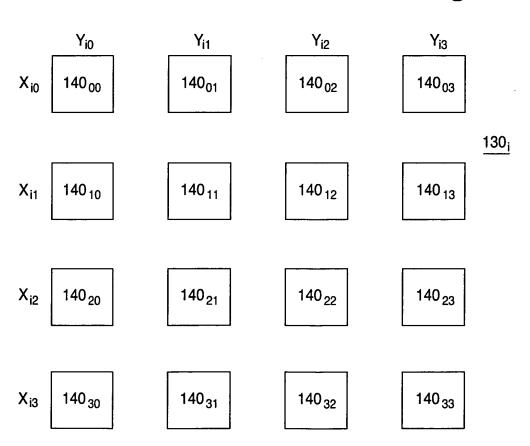


Fig. 11

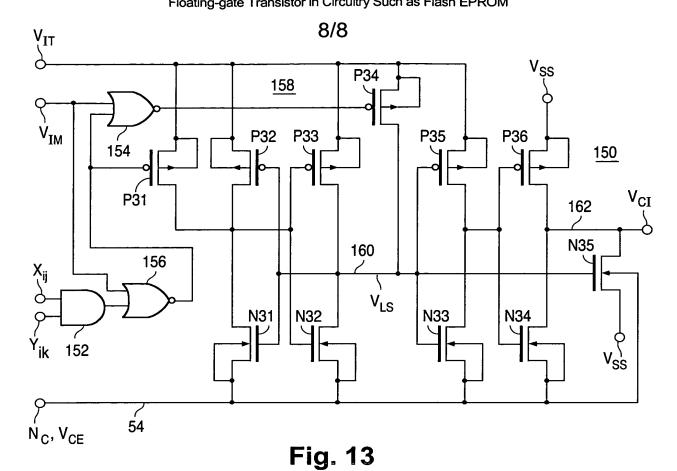
Fig. 12



REPLACEMENT SHEET

Inventor: Park, Jongram Appl'n No.: 10/780,030

Title: Voltage Discharge Technique for Controlling Threshold voltage Characteristics of Floating-gate Transistor in Circuitry Such as Flash EPROM



64 P41 P42  $N_B$ ,  $V_{BE}$ 170 P43  $V_{DD}$  $V_{\mathsf{BL}}$ N41 70 R21-174 N44 V<sub>EI</sub> N43 N42 172  $V_{SS}$ V<sub>SS</sub> V<sub>SS</sub>~ Fig. 14